

## ABSTRACT OF THE DISCLOSURE

The present invention relates to a removal cleaning method for a semiconductor substrate or a semiconductor device with metal wirings by using a 5 remover composition, wherein the remover composition contains a dissolution agent having an alumina dissolution amount as measured according to the standard test (A-1) of 10 ppm or more, and an inhibitor having an aluminum etching amount as measured according to the standard test (B-1) of 7 nm or less, and the remover composition substantially does not contain a fluorine-containing 10 compound; a method of producing a semiconductor substrate or a semiconductor device, including the step involving the removal cleaning method; and a remover composition containing a specified acid, and a specified inorganic acid salt and/or organic acid salt. The removal cleaning method and the remover 15 composition of the present invention can be suitably used for producing even higher-speed, even more highly integrated and high quality electronic parts such as LCDs, memories and CPUs, particularly for cleaning a semiconductor substrate or a semiconductor device in which a wiring material containing aluminum and/or titanium is used.